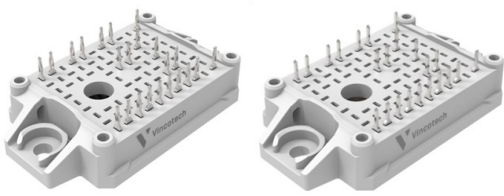
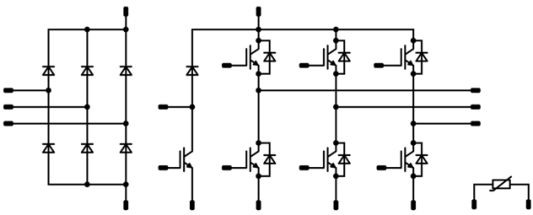




Vincotech

10-EZ12PMA025M7-L929A78T 10-E112PMA025M7-L929A78Z

datasheet

flowPIM E1		1200 V / 25 A
Features • IGBT M7 with low V_{CEsat} and improved EMC behavior • Standard industrial housing • Optimized $R_{th(j-s)}$ with Phase Change Material • Built-in NTC		flow E1 12 mm housing  Press-fit pin Solder pin
Target applications • Industrial Drives		Schematic 
Types • 10-EZ12PMA025M7-L929A78T • 10-E112PMA025M7-L929A78Z		

Maximum Ratings

$T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Inverter Switch				
Collector-emitter voltage	V_{CES}		1200	V
Collector current	I_C	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	33	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}	50	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	79	W
Gate-emitter voltage	V_{GES}		±20	V
Short circuit ratings	t_{SC}	$V_{GE} = 15\text{ V}$ $V_{ce} = 800\text{ V}$ $T_j = 150\text{ °C}$	9,5	µs
Maximum junction temperature	T_{jmax}		175	°C



Vincotech

10-EZ12PMA025M7-L929A78T
10-E112PMA025M7-L929A78Z
 datasheet

Maximum Ratings

$T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
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Inverter Diode

Peak repetitive reverse voltage	V_{RRM}		1200	V
Continuous (direct) forward current	I_F	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	35	A
Repetitive peak forward current	I_{FRM}	T_j limited by T_{jmax}	50	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	71	W
Maximum junction temperature	T_{jmax}		175	°C

Brake Switch

Collector-emitter voltage	V_{CES}		1200	V
Collector current	I_C	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	33	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}	50	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	79	W
Gate-emitter voltage	V_{GES}		±20	V
Short circuit ratings	t_{SC}	$V_{GE} = 15\text{ V}$ $V_{CE} = 800\text{ V}$ $T_j = 150\text{ °C}$	9,5	µs
Maximum junction temperature	T_{jmax}		175	°C

Brake Diode

Peak repetitive reverse voltage	V_{RRM}		1200	V
Continuous (direct) forward current	I_F	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	14	A
Repetitive peak forward current	I_{FRM}	T_j limited by T_{jmax}	20	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	43	W
Maximum junction temperature	T_{jmax}		175	°C

Rectifier Diode

Peak repetitive reverse voltage	V_{RRM}		1600	V
Continuous (direct) forward current	I_F	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	47	A
Surge (non-repetitive) forward current	I_{FSM}	50 Hz Single Half Sine Wave $t_p = 10\text{ ms}$ $T_j = 150\text{ °C}$	270	A
Surge current capability	I^2t		370	A²s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	58	W
Maximum junction temperature	T_{jmax}		150	°C



Vincotech

10-EZ12PMA025M7-L929A78T
10-E112PMA025M7-L929A78Z
datasheet

Maximum Ratings

$T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
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Module Properties

Thermal Properties

Storage temperature	T_{stg}		-40...+125	°C
Operation temperature under switching condition	T_{top}		-40...(T_{jmax} - 25)	°C

Isolation Properties

Isolation voltage	V_{isol}	DC Test Voltage* $t_p = 2\text{ s}$	6000	V
		AC Voltage $t_p = 1\text{ min}$	2500	V
Creepage distance			min. 12,7	mm
Clearance			min. 12,7	mm
Comparative Tracking Index	CTI		≥ 600	

*100 % tested in production



Vincotech

10-EZ12PMA025M7-L929A78T
10-E112PMA025M7-L929A78Z
 datasheet

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	

Inverter Switch

Static

Gate-emitter threshold voltage	$V_{GE(th)}$			10	0,0025	25	5,4	6,0	6,6	V
Collector-emitter saturation voltage	V_{CEsat}		15		25	25 125 150		1,65 1,89 1,95	2,15	V
Collector-emitter cut-off current	I_{CES}		0	1200		25			70	μA
Gate-emitter leakage current	I_{GES}		20	0		25			500	nA
Internal gate resistance	r_g							none		Ω
Input capacitance	C_{ies}		0	10		25		4800		pF
Output capacitance	C_{oes}							170		
Reverse transfer capacitance	C_{res}							57		
Gate charge	Q_g		15	600	25	25		180		nC

Thermal

Thermal resistance junction to sink	$R_{th(j-s)}$	$\lambda_{paste} = 3,4 \text{ W/mK}$ (PSX)						1,20		K/W
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Dynamic

Turn-on delay time	$t_{d(on)}$	$R_{gon} = 16 \Omega$ $R_{goff} = 16 \Omega$	± 15	600	25	25 125 150		147 149 145		ns
Rise time	t_r					25 125 150		29 33 34		
Turn-off delay time	$t_{d(off)}$					25 125 150		171 191 196		
Fall time	t_f					25 125 150		95 110 115		
Turn-on energy (per pulse)*	E_{on}					25 125 150		2,06 2,66 2,82		mWs
Turn-off energy (per pulse)*	E_{off}					25 125 150		1,67 2,18 2,29		

* $L_s = 14 \text{ nH}$



Vincotech

10-EZ12PMA025M7-L929A78T
10-E112PMA025M7-L929A78Z
 datasheet

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	

Inverter Diode

Static

Forward voltage	V_F				25	25 125 150		1,63 1,70 1,69	2,1	V
Reverse leakage current	I_R			1200		25			35	μA

Thermal

Thermal resistance junction to sink	$R_{th(j-s)}$	$\lambda_{paste} = 3,4 \text{ W/mK}$ (PSX)						1,34		K/W
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Dynamic

Peak recovery current	I_{RRM}	$di/dt = 645 \text{ A/}\mu\text{s}$ $di/dt = 673 \text{ A/}\mu\text{s}$ $di/dt = 633 \text{ A/}\mu\text{s}$	± 15	600	25	25 125 150		21 23 23		A
Reverse recovery time	t_{rr}					25 125 150		254 367 404		ns
Recovered charge	Q_r					25 125 150		2,54 3,88 4,28		μC
Reverse recovered energy	E_{rec}					25 125 150		0,88 1,45 1,61		mWs
Peak rate of fall of recovery current	$(di_{rt}/dt)_{max}$					25 125 150		217 134 132		A/μs



Vincotech

10-EZ12PMA025M7-L929A78T
10-E112PMA025M7-L929A78Z
 datasheet

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	

Brake Switch

Static

Gate-emitter threshold voltage	$V_{GE(th)}$			10	0,0025	25	5,4	6,0	6,6	V
Collector-emitter saturation voltage	V_{CEsat}		15		25	25 125 150		1,65 1,89 1,95	2,15	V
Collector-emitter cut-off current	I_{CES}		0	1200		25			70	μA
Gate-emitter leakage current	I_{GES}		20	0		25			500	nA
Internal gate resistance	r_g							none		Ω
Input capacitance	C_{ies}		0	10		25		4800		pF
Output capacitance	C_{oes}							170		
Reverse transfer capacitance	C_{res}							57		
Gate charge	Q_g		15	600	25	25		180		nC

Thermal

Thermal resistance junction to sink	$R_{th(j-s)}$	$\lambda_{paste} = 3,4 \text{ W/mK}$ (PSX)						1,20		K/W
-------------------------------------	---------------	---	--	--	--	--	--	------	--	-----

Dynamic

Turn-on delay time	$t_{d(on)}$	$R_{gon} = 32 \Omega$ $R_{goff} = 32 \Omega$	± 15	600	25	25 125 150		403 389 382		ns
Rise time	t_r					25 125 150		109 117 120		
Turn-off delay time	$t_{d(off)}$					25 125 150		208 233 240		
Fall time	t_f					25 125 150		81 93 96		
Turn-on energy (per pulse)	E_{on}					25 125 150		3,05 3,62 3,79		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		1,67 2,23 2,39		



Vincotech

10-EZ12PMA025M7-L929A78T
10-E112PMA025M7-L929A78Z
 datasheet

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	

Brake Diode

Static

Forward voltage	V_F				10	25 125 150		1,61 1,69 1,69	2,1	V
Reverse leakage current	I_R			1200		25			25	µA

Thermal

Thermal resistance junction to sink	$R_{th(j-s)}$	$\lambda_{paste} = 3,4 \text{ W/mK (PSX)}$						2,19		K/W
-------------------------------------	---------------	--	--	--	--	--	--	------	--	-----

Dynamic

Peak recovery current	I_{RRM}	$di/dt = 207 \text{ A/}\mu\text{s}$ $di/dt = 210 \text{ A/}\mu\text{s}$ $di/dt = 196 \text{ A/}\mu\text{s}$	± 15	600	25	25 125 150		9 10 10		A
Reverse recovery time	t_{rr}					25 125 150		317 448 499		ns
Recovered charge	Q_r					25 125 150		1,54 2,34 2,61		µC
Reverse recovered energy	E_{rec}					25 125 150		0,518 0,867 0,980		mWs
Peak rate of fall of recovery current	$(di_{rt}/dt)_{max}$					25 125 150		52 38 38		A/µs

Rectifier Diode

Static

Forward voltage	V_F				35	25 125		1,17 1,13		V
Reverse leakage current	I_R			1600		25			50	µA

Thermal

Thermal resistance junction to sink	$R_{th(j-s)}$	$\lambda_{paste} = 3,4 \text{ W/mK (PSX)}$						1,20		K/W
-------------------------------------	---------------	--	--	--	--	--	--	------	--	-----



Vincotech

10-EZ12PMA025M7-L929A78T
10-E112PMA025M7-L929A78Z
 datasheet

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	

Thermistor

Rated resistance	R					25		5		kΩ
Deviation of R_{100}	$\Delta_{R/R}$	$R_{100} = 493 \Omega$				100	-5		+5	%
Power dissipation	P					25		245		mW
Power dissipation constant						25		1,4		mW/K
B-value	$B_{(25/50)}$	Tol. $\pm 2 \%$				25		3375		K
B-value	$B_{(25/100)}$	Tol. $\pm 2 \%$				25		3437		K
Vincotech NTC Reference									K	



Vincotech

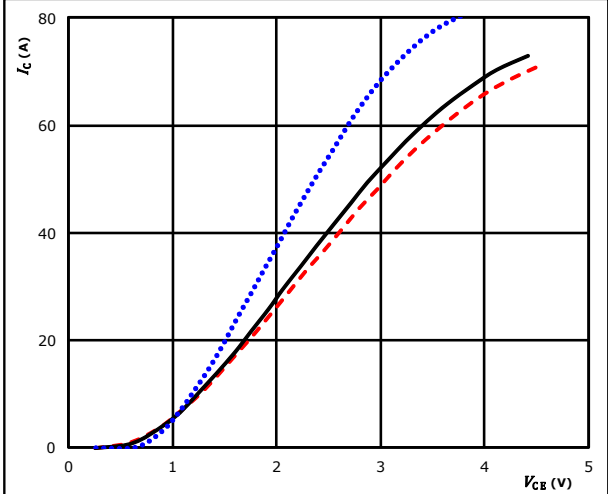
10-EZ12PMA025M7-L929A78T 10-E112PMA025M7-L929A78Z datasheet

Inverter Switch Characteristics

figure 1. IGBT

Typical output characteristics

$$I_C = f(V_{CE})$$

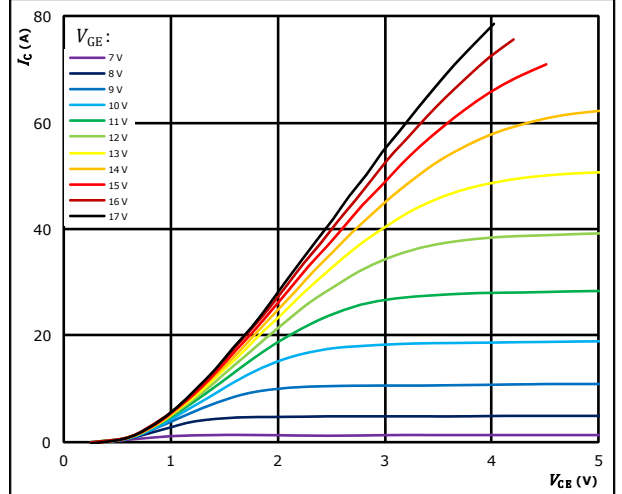


$t_p = 250 \mu s$
 $V_{GE} = 15 V$
 $T_j: 25 \text{ } ^\circ C$ (dotted blue)
 $125 \text{ } ^\circ C$ (solid black)
 $150 \text{ } ^\circ C$ (dashed red)

figure 2. IGBT

Typical output characteristics

$$I_C = f(V_{CE})$$

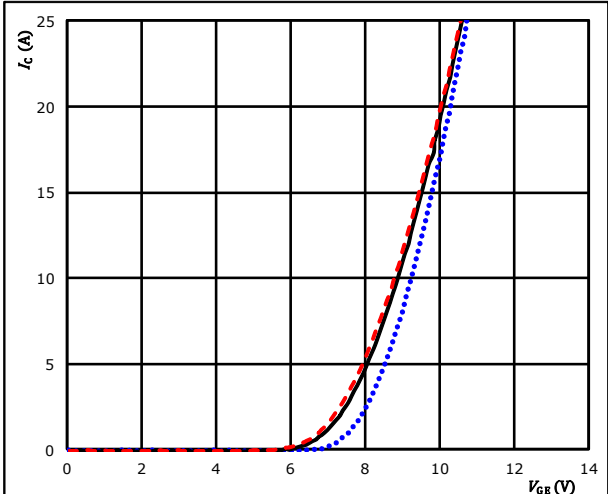


$t_p = 250 \mu s$
 $T_j = 125 \text{ } ^\circ C$
 V_{GE} from 7 V to 17 V in steps of 1 V

figure 3. IGBT

Typical transfer characteristics

$$I_C = f(V_{GE})$$

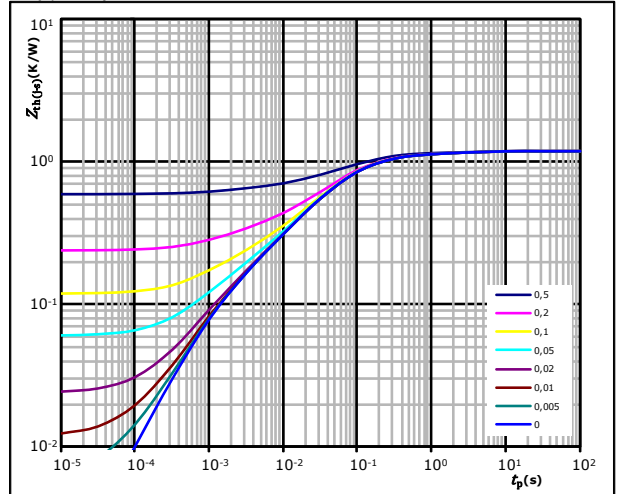


$t_p = 100 \mu s$
 $V_{CE} = 10 V$
 $T_j: 25 \text{ } ^\circ C$ (dotted blue)
 $125 \text{ } ^\circ C$ (solid black)
 $150 \text{ } ^\circ C$ (dashed red)

figure 4. IGBT

Transient thermal impedance as function of pulse duration

$$Z_{th(j-s)} = f(t_p)$$



$D = t_p / T$
 $R_{th(j-s)} = 1,20 \text{ K/W}$
IGBT thermal model values

$R \text{ (K/W)}$	$\tau \text{ (s)}$
7,19E-02	2,96E+00
1,76E-01	3,16E-01
6,46E-01	6,48E-02
2,16E-01	1,08E-02
8,54E-02	1,15E-03



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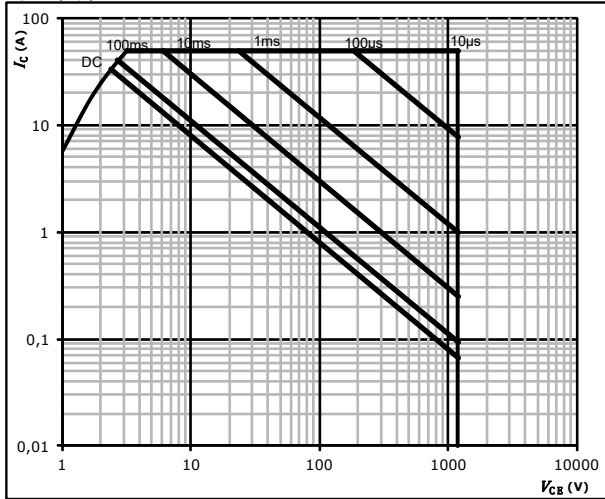
10-EZ12PMA025M7-L929A78T
10-E112PMA025M7-L929A78Z
datasheet

Inverter Switch Characteristics

figure 5. IGBT

Safe operating area

$$I_C = f(V_{CE})$$



$D =$ single pulse
 $T_s =$ 80 °C
 $V_{GE} =$ ±15 V
 $T_j =$ T_{jmax}



Vincotech

10-EZ12PMA025M7-L929A78T
10-E112PMA025M7-L929A78Z
 datasheet

Inverter Diode Characteristics

figure 1. FWD

Typical forward characteristics

$$I_F = f(V_F)$$

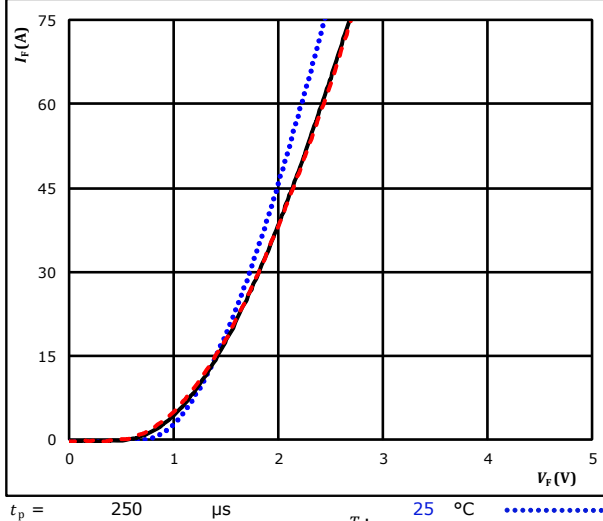
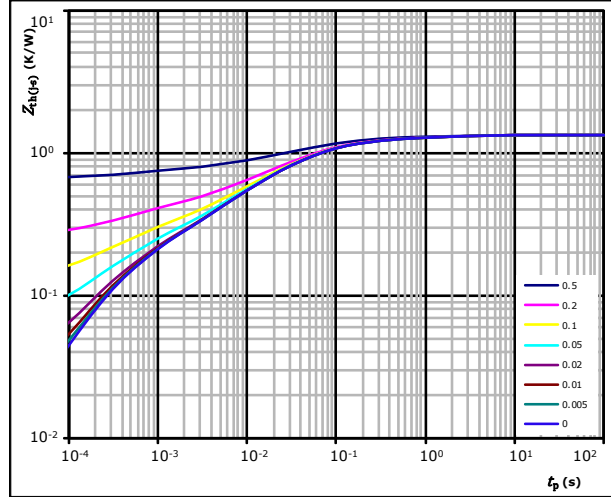


figure 2. FWD

Transient thermal impedance as a function of pulse width

$$Z_{th(j-s)} = f(t_p)$$



FWD thermal model values

$R \text{ (K/W)}$	$\tau \text{ (s)}$
7,90E-02	2,29E+00
1,38E-01	2,89E-01
5,15E-01	5,53E-02
3,34E-01	1,22E-02
1,30E-01	2,48E-03
1,40E-01	3,42E-04



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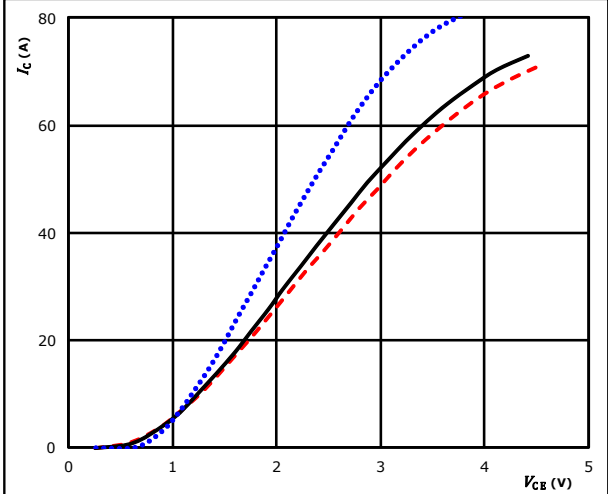
10-EZ12PMA025M7-L929A78T 10-E112PMA025M7-L929A78Z datasheet

Brake Switch Characteristics

figure 1. IGBT

Typical output characteristics

$$I_C = f(V_{CE})$$

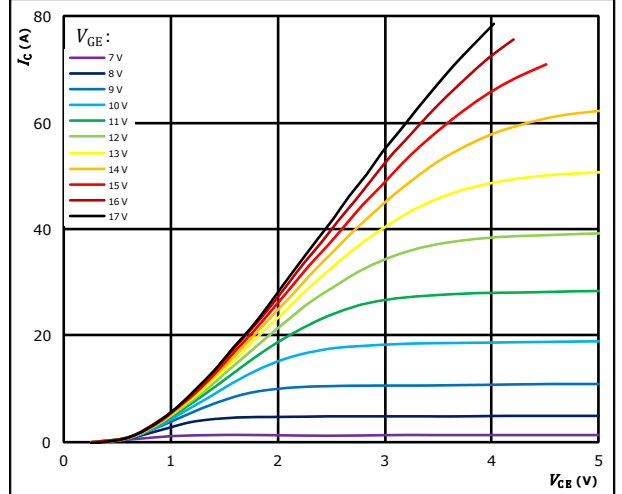


$t_p = 250 \mu s$
 $V_{GE} = 15 V$
 $T_j: 25 \text{ } ^\circ C$ (blue dotted)
 $125 \text{ } ^\circ C$ (black solid)
 $150 \text{ } ^\circ C$ (red dashed)

figure 2. IGBT

Typical output characteristics

$$I_C = f(V_{CE})$$

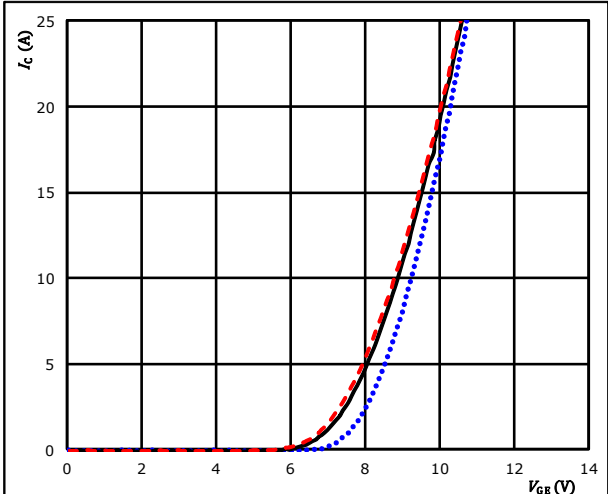


$t_p = 250 \mu s$
 $T_j = 125 \text{ } ^\circ C$
 V_{GE} from 7 V to 17 V in steps of 1 V

figure 3. IGBT

Typical transfer characteristics

$$I_C = f(V_{GE})$$

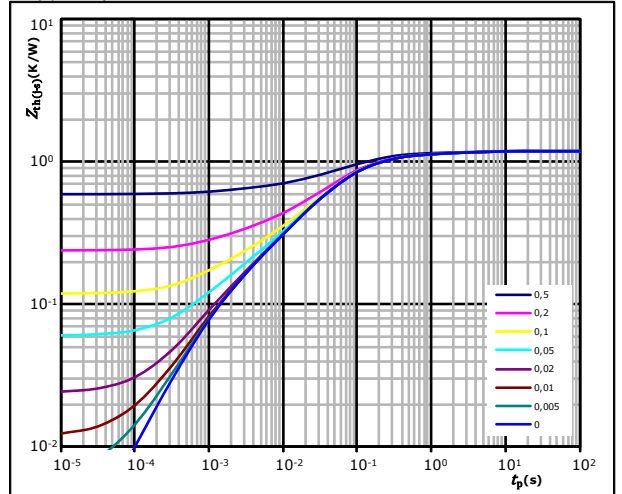


$t_p = 100 \mu s$
 $V_{CE} = 10 V$
 $T_j: 25 \text{ } ^\circ C$ (blue dotted)
 $125 \text{ } ^\circ C$ (black solid)
 $150 \text{ } ^\circ C$ (red dashed)

figure 4. IGBT

Transient thermal impedance as function of pulse duration

$$Z_{th(j-s)} = f(t_p)$$



$D = t_p / T$
 $R_{th(j-s)} = 1,20 \text{ K/W}$
IGBT thermal model values

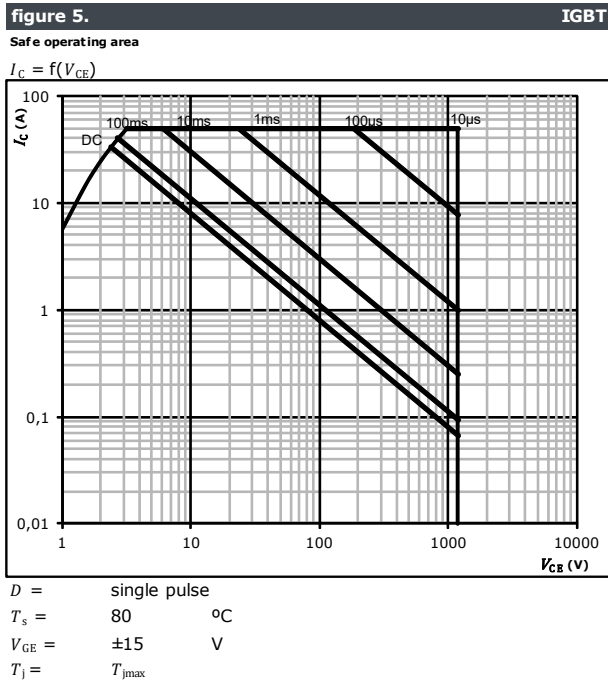
$R \text{ (K/W)}$	$\tau \text{ (s)}$
7,19E-02	2,96E+00
1,76E-01	3,16E-01
6,46E-01	6,48E-02
2,16E-01	1,08E-02
8,54E-02	1,15E-03



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10-EZ12PMA025M7-L929A78T
10-E112PMA025M7-L929A78Z
datasheet

Brake Switch Characteristics





Vincotech

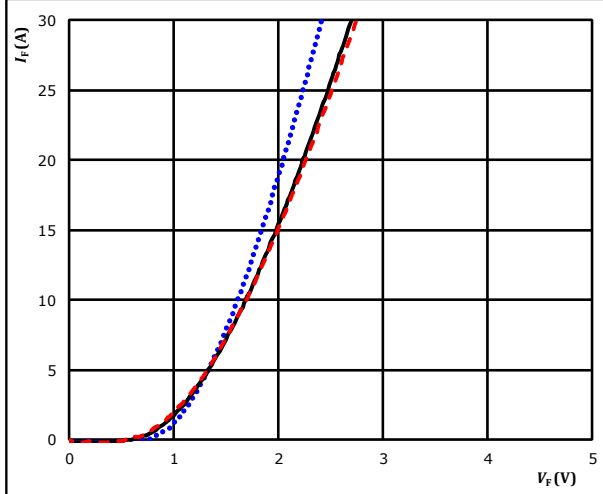
10-EZ12PMA025M7-L929A78T
10-E112PMA025M7-L929A78Z
datasheet

Brake Diode Characteristics

figure 1. FWD

Typical forward characteristics

$$I_F = f(V_F)$$

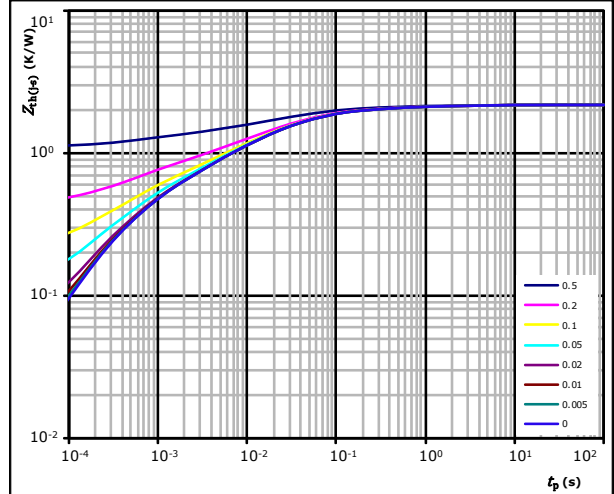


$t_p = 250 \mu s$
 T_j : 25 °C (blue dotted line)
125 °C (black solid line)
150 °C (red dashed line)

figure 2. FWD

Transient thermal impedance as a function of pulse width

$$Z_{th(j-s)} = f(t_p)$$



$$D = \frac{t_p}{T}$$

$$R_{th(j-s)} = 2,19 \text{ K/W}$$

FWD thermal model values

R (K/W)	τ (s)
8,09E-02	3,20E+00
2,08E-01	2,82E-01
6,85E-01	4,41E-02
5,92E-01	1,02E-02
3,27E-01	2,02E-03
2,95E-01	3,64E-04



Vincotech

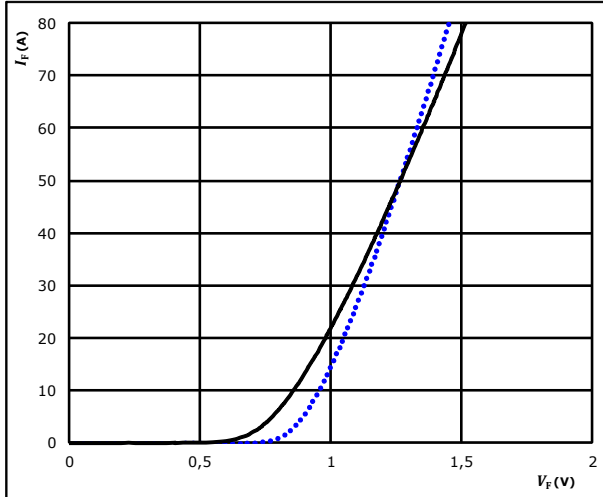
10-EZ12PMA025M7-L929A78T
10-E112PMA025M7-L929A78Z
 datasheet

Rectifier Diode Characteristics

figure 1. FWD

Typical forward characteristics

$$I_F = f(V_F)$$

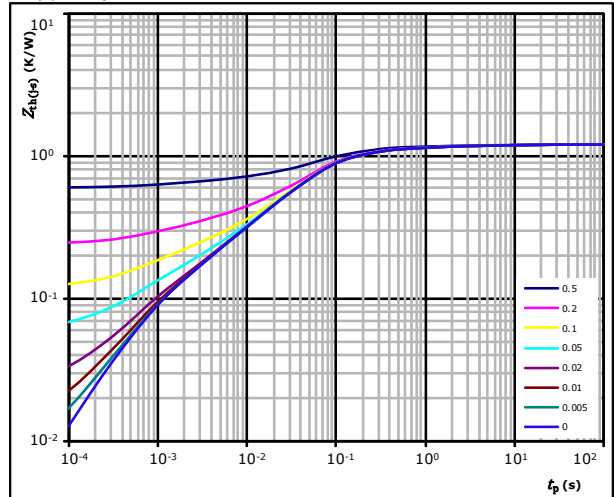


$t_p = 250 \mu s$ $T_j: 25 \text{ } ^\circ\text{C}$ (dotted blue line) $125 \text{ } ^\circ\text{C}$ (solid black line)

figure 2. FWD

Transient thermal impedance as a function of pulse width

$$Z_{th(j-s)} = f(t_p)$$



$$D = t_p / T$$

$$R_{th(j-s)} = 1,20 \text{ K/W}$$

FWD thermal model values

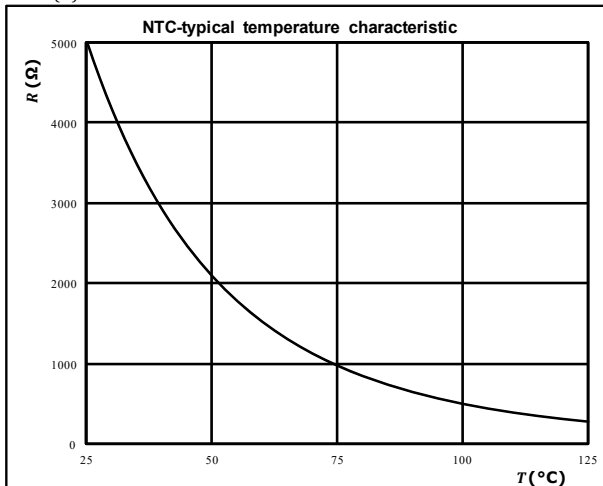
R (K/W)	τ (s)
3,54E-02	9,31E+00
8,09E-02	9,99E-01
2,12E-01	1,71E-01
6,76E-01	4,85E-02
1,19E-01	5,88E-03
7,98E-02	8,33E-04

Thermistor Characteristics

figure 1. Thermistor

Typical NTC characteristic
 as a function of temperature

$$R = f(T)$$





Vincotech

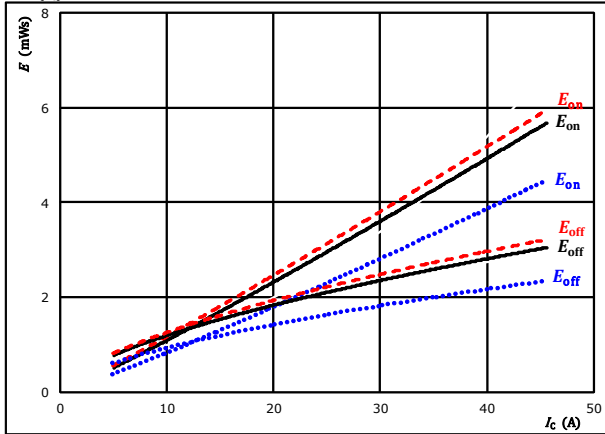
10-EZ12PMA025M7-L929A78T 10-E112PMA025M7-L929A78Z datasheet

Inverter Switching Characteristics

figure 1. IGBT

Typical switching energy losses as a function of collector current

$$E = f(I_C)$$



With an inductive load at

$V_{CE} = 600$ V

$V_{GE} = \pm 15$ V

$R_{g\text{on}} = 16$ Ω

$R_{g\text{off}} = 16$ Ω

T_j :

25 °C

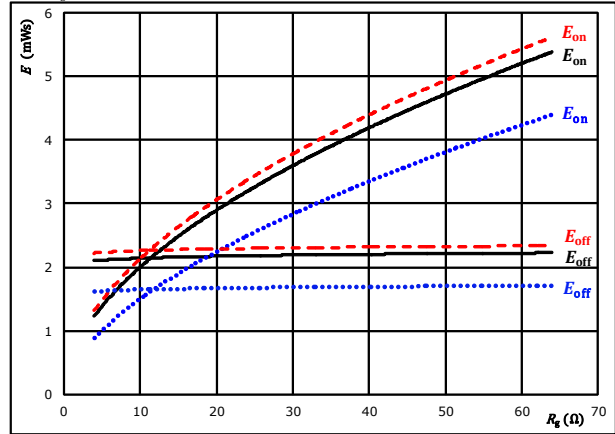
125 °C

150 °C

figure 2. IGBT

Typical switching energy losses as a function of gate resistor

$$E = f(R_g)$$



With an inductive load at

$V_{CE} = 600$ V

$V_{GE} = \pm 15$ V

$I_C = 25$ A

T_j :

25 °C

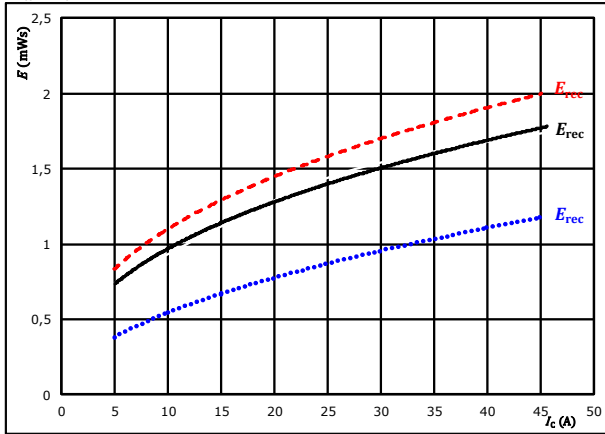
125 °C

150 °C

figure 3. FWD

Typical reverse recovered energy loss as a function of collector current

$$E_{\text{rec}} = f(I_C)$$



With an inductive load at

$V_{CE} = 600$ V

$V_{GE} = \pm 15$ V

$R_{g\text{on}} = 16$ Ω

T_j :

25 °C

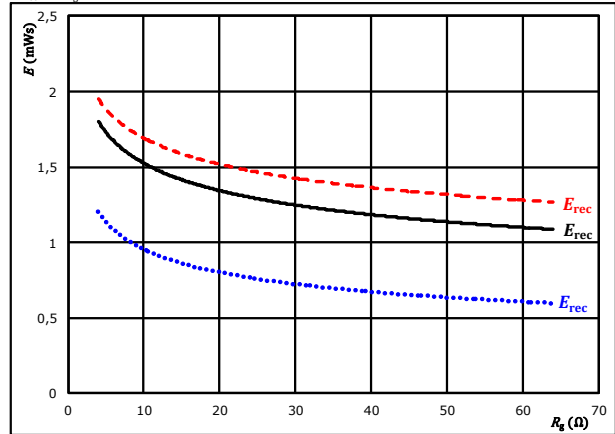
125 °C

150 °C

figure 4. FWD

Typical reverse recovered energy loss as a function of gate resistor

$$E_{\text{rec}} = f(R_g)$$



With an inductive load at

$V_{CE} = 600$ V

$V_{GE} = \pm 15$ V

$I_C = 25$ A

T_j :

25 °C

125 °C

150 °C



Vincotech

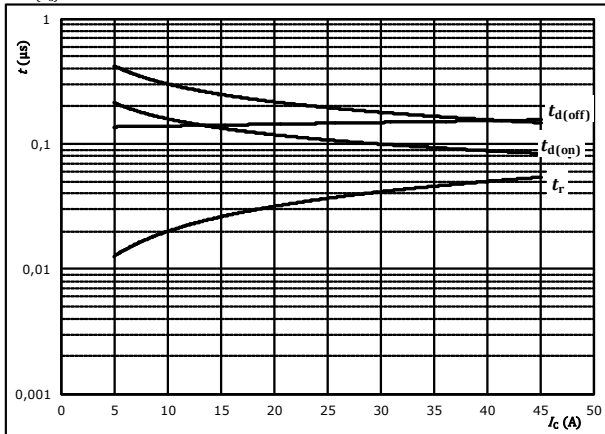
10-EZ12PMA025M7-L929A78T
10-E112PMA025M7-L929A78Z
datasheet

Inverter Switching Characteristics

figure 5. IGBT

Typical switching times as a function of collector current

$$t = f(I_C)$$



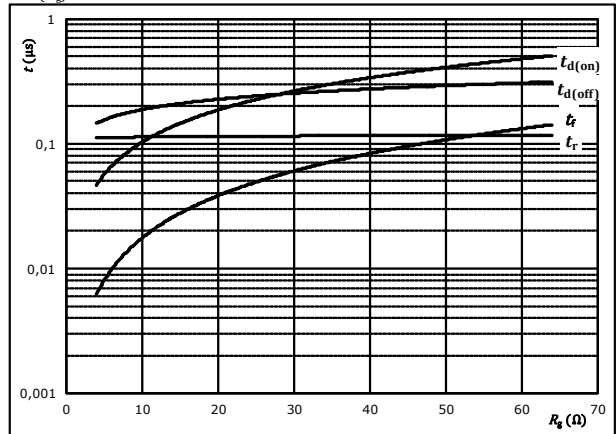
With an inductive load at

$T_j =$	150	°C
$V_{CE} =$	600	V
$V_{GE} =$	±15	V
$R_{gon} =$	16	Ω
$R_{goff} =$	16	Ω

figure 6. IGBT

Typical switching times as a function of gate resistor

$$t = f(R_g)$$



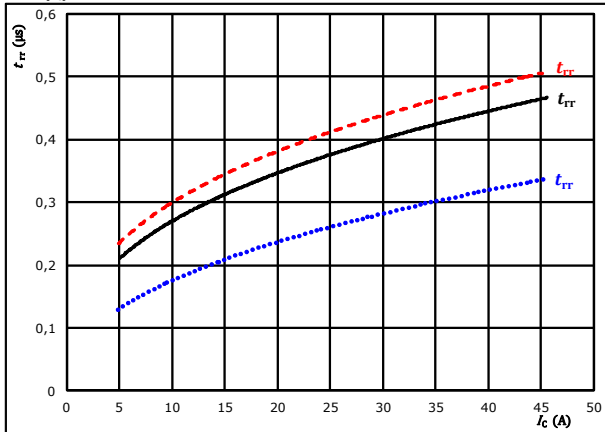
With an inductive load at

$T_j =$	150	°C
$V_{CE} =$	600	V
$V_{GE} =$	±15	V
$I_C =$	25	A

figure 7. FWD

Typical reverse recovery time as a function of collector current

$$t_{rr} = f(I_C)$$

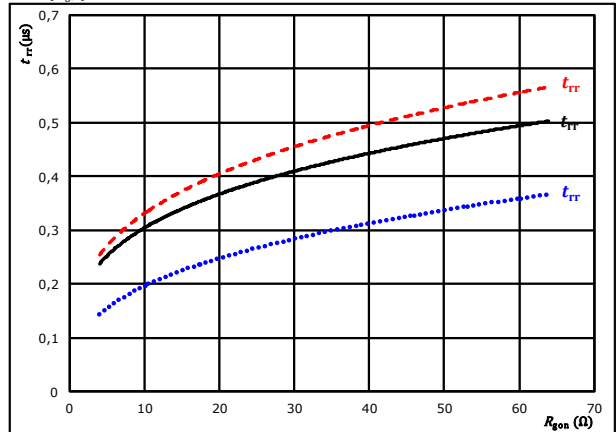


At	$V_{CE} =$	600	V	$T_j:$	25 °C	
	$V_{GE} =$	±15	V		125 °C	————
	$R_{gon} =$	16	Ω		150 °C	-----

figure 8. FWD

Typical reverse recovery time as a function of IGBT turn on gate resistor

$$t_{rr} = f(R_{gon})$$



At	$V_{CE} =$	600	V	$T_j:$	25 °C	
	$V_{GE} =$	±15	V		125 °C	————
	$I_C =$	25	A		150 °C	-----



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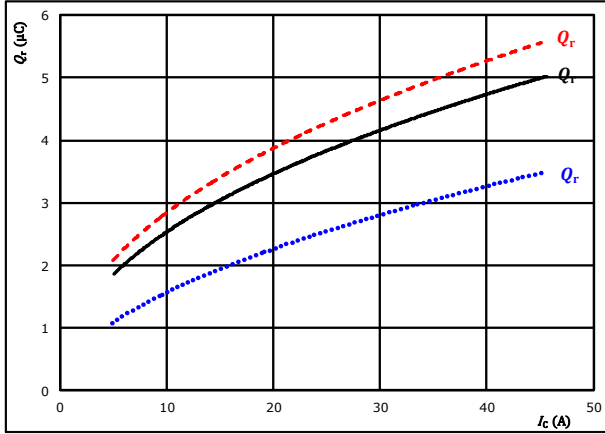
10-EZ12PMA025M7-L929A78T
10-E112PMA025M7-L929A78Z
 datasheet

Inverter Switching Characteristics

figure 9. FWD

Typical recovered charge as a function of collector current

$$Q_r = f(I_C)$$

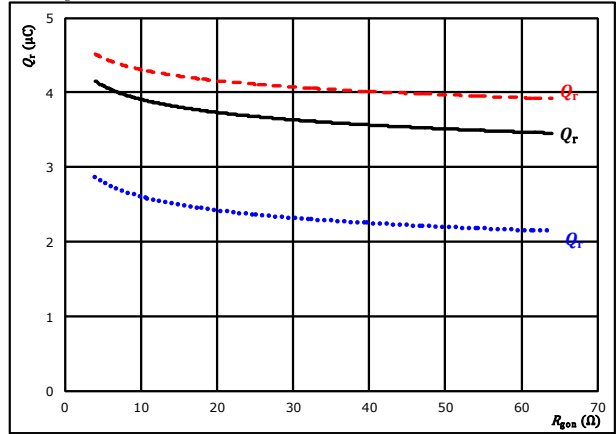


At $V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $R_{gon} = 16$ Ω
 $T_j: 25$ °C (dotted blue), 125 °C (solid black), 150 °C (dashed red)

figure 10. FWD

Typical recovered charge as a function of IGBT turn on gate resistor

$$Q_r = f(R_{gon})$$

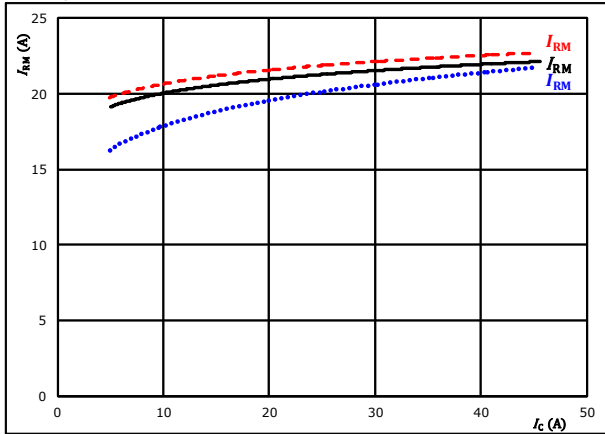


At $V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $I_C = 25$ A
 $T_j: 25$ °C (dotted blue), 125 °C (solid black), 150 °C (dashed red)

figure 11. FWD

Typical peak reverse recovery current as a function of collector current

$$I_{RM} = f(I_C)$$

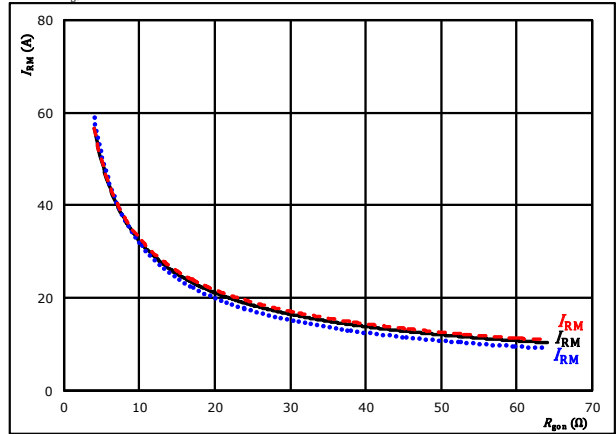


At $V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $R_{gon} = 16$ Ω
 $T_j: 25$ °C (dotted blue), 125 °C (solid black), 150 °C (dashed red)

figure 12. FWD

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

$$I_{RM} = f(R_{gon})$$



At $V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $I_C = 25$ A
 $T_j: 25$ °C (dotted blue), 125 °C (solid black), 150 °C (dashed red)



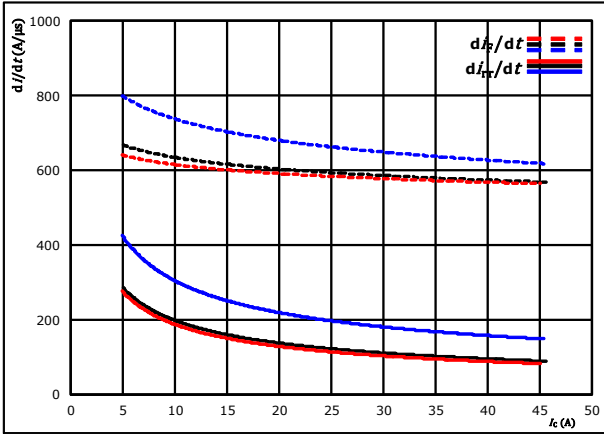
Vincotech

10-EZ12PMA025M7-L929A78T 10-E112PMA025M7-L929A78Z datasheet

Inverter Switching Characteristics

figure 13. FWD

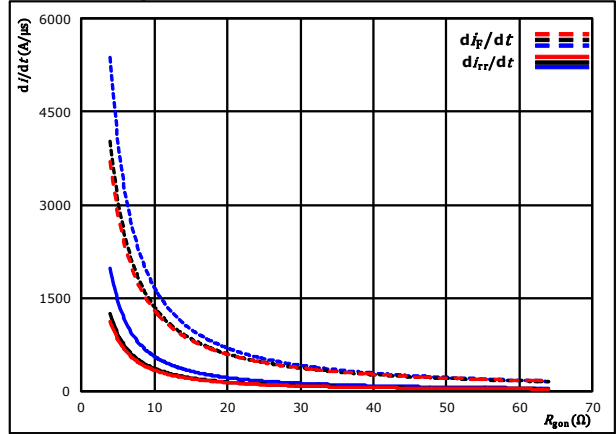
Typical rate of fall of forward and reverse recovery current as a function of collector current
 $di_F/dt, di_{rr}/dt = f(I_C)$



At $V_{CE} = 600$ V $T_J = 25$ °C
 $V_{GE} = \pm 15$ V $T_J = 125$ °C
 $R_{gon} = 16$ Ω $T_J = 150$ °C

figure 14. FWD

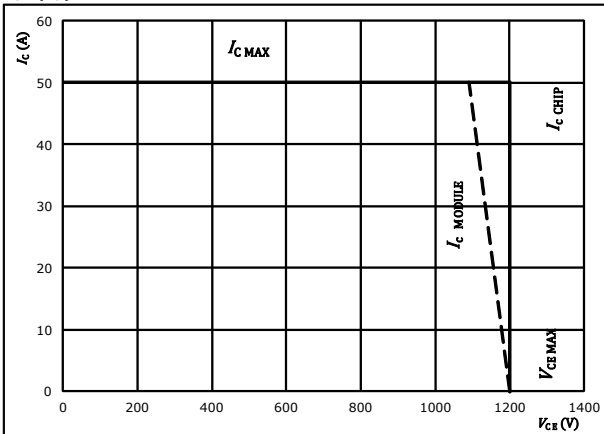
Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor
 $di_F/dt, di_{rr}/dt = f(R_{gon})$



At $V_{CE} = 600$ V $T_J = 25$ °C
 $V_{GE} = \pm 15$ V $T_J = 125$ °C
 $I_C = 25$ A $T_J = 150$ °C

figure 15. IGBT

Reverse bias safe operating area
 $I_C = f(V_{CE})$



At $T_J = 125$ °C
 $R_{gon} = 16$ Ω
 $R_{goff} = 16$ Ω



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10-E112PMA025M7-L929A78Z
 datasheet

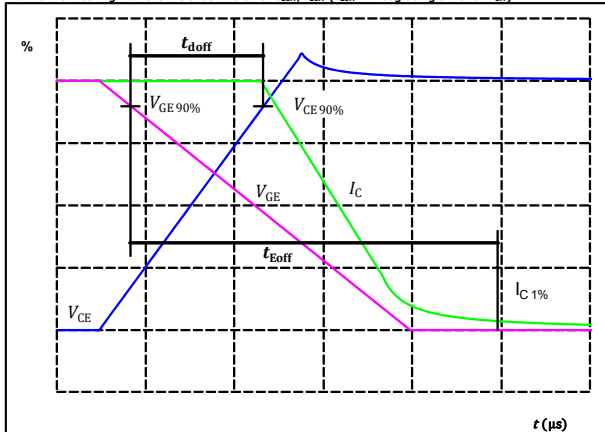
Inverter Switching Definitions

General conditions

T_j	=	125 °C
R_{gon}	=	16 Ω
R_{goff}	=	16 Ω

figure 1. IGBT

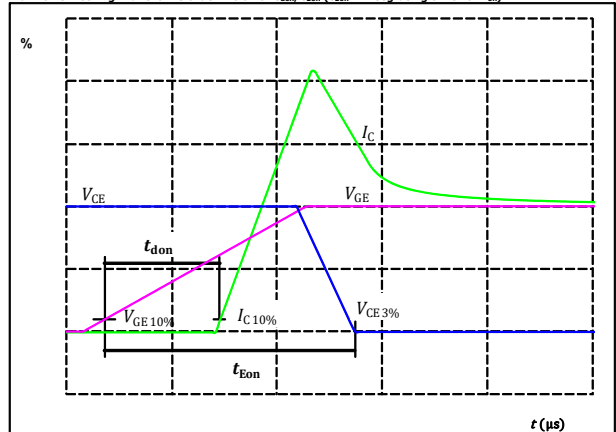
Turn-off Switching Waveforms & definition of t_{doff} , t_{Eoff} (t_{Eoff} = integrating time for E_{off})



$V_{GE}(0\%) =$	-15	V
$V_{GE}(100\%) =$	15	V
$V_C(100\%) =$	600	V
$I_C(100\%) =$	25	A
$t_{doff} =$	191	ns

figure 2. IGBT

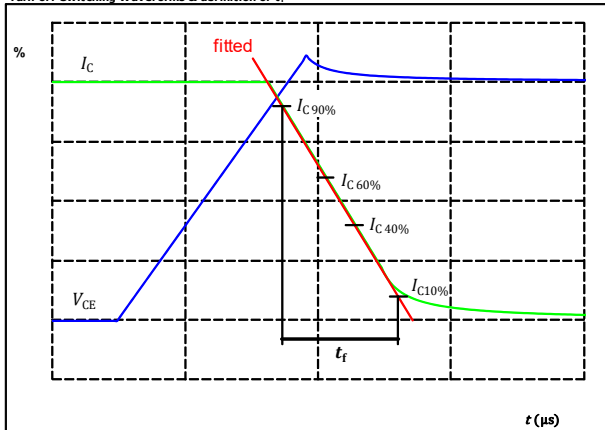
Turn-on Switching Waveforms & definition of t_{don} , t_{Eon} (t_{Eon} = integrating time for E_{on})



$V_{GE}(0\%) =$	-15	V
$V_{GE}(100\%) =$	15	V
$V_C(100\%) =$	600	V
$I_C(100\%) =$	25	A
$t_{don} =$	149	ns

figure 3. IGBT

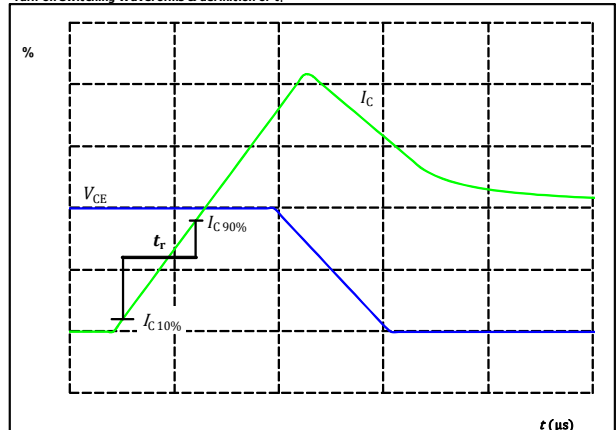
Turn-off Switching Waveforms & definition of t_f



$V_C(100\%) =$	600	V
$I_C(100\%) =$	25	A
$t_f =$	110	ns

figure 4. IGBT

Turn-on Switching Waveforms & definition of t_r



$V_C(100\%) =$	600	V
$I_C(100\%) =$	25	A
$t_r =$	33	ns

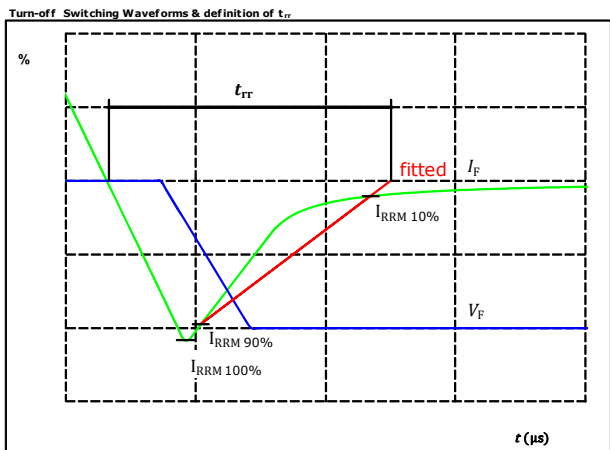


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10-EZ12PMA025M7-L929A78T
10-E112PMA025M7-L929A78Z
 datasheet

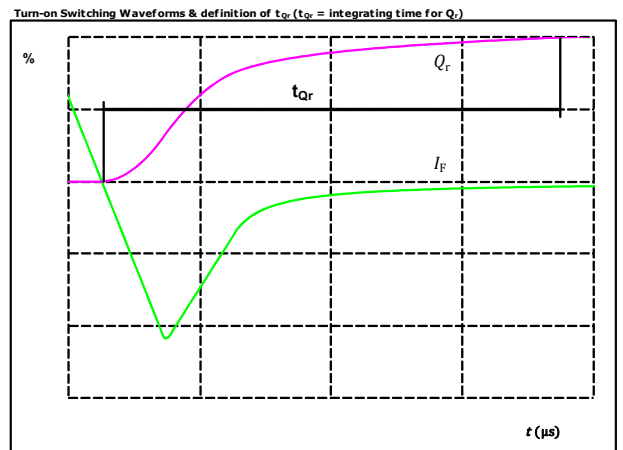
Inverter Switching Characteristics

figure 5. FWD



$V_F(100\%) =$	600	V
$I_F(100\%) =$	25	A
$I_{RRM}(100\%) =$	23	A
$t_{rr} =$	367	ns

figure 6. FWD



$I_F(100\%) =$	25	A
$Q_r(100\%) =$	3,88	μC



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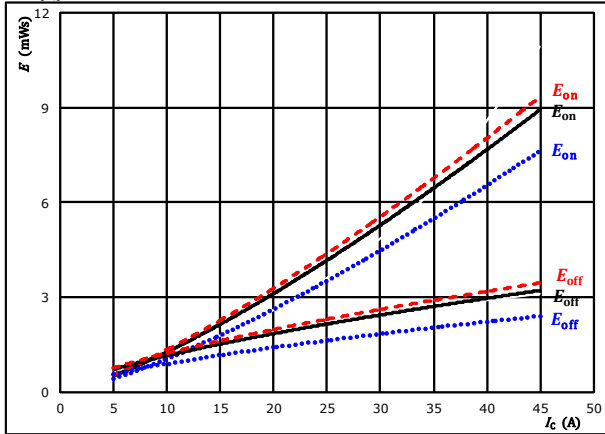
10-EZ12PMA025M7-L929A78T 10-E112PMA025M7-L929A78Z datasheet

Brake Switching Characteristics

figure 1. IGBT

Typical switching energy losses as a function of collector current

$$E = f(I_C)$$



With an inductive load at

$V_{CE} = 600$ V

$V_{GE} = \pm 15$ V

$R_{g\text{on}} = 32$ Ω

$R_{g\text{off}} = 32$ Ω

T_j :

25 °C

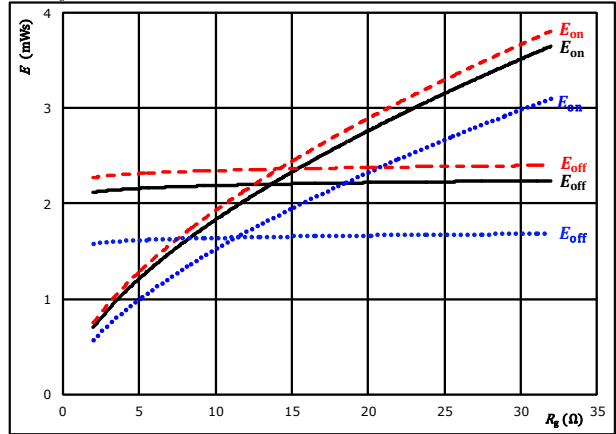
125 °C

150 °C

figure 2. IGBT

Typical switching energy losses as a function of gate resistor

$$E = f(R_g)$$



With an inductive load at

$V_{CE} = 600$ V

$V_{GE} = \pm 15$ V

$I_C = 25$ A

T_j :

25 °C

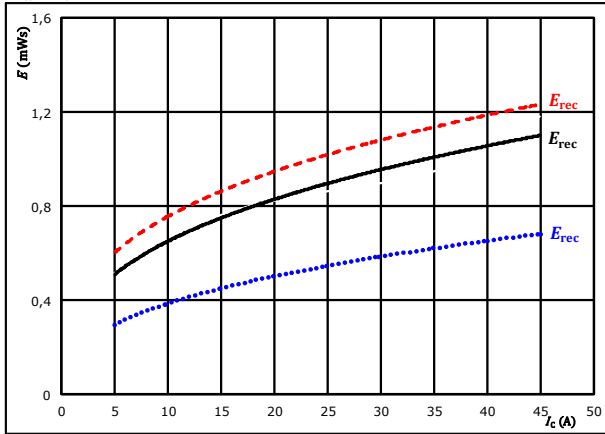
125 °C

150 °C

figure 3. FWD

Typical reverse recovered energy loss as a function of collector current

$$E_{rec} = f(I_C)$$



With an inductive load at

$V_{CE} = 600$ V

$V_{GE} = \pm 15$ V

$R_{g\text{on}} = 32$ Ω

T_j :

25 °C

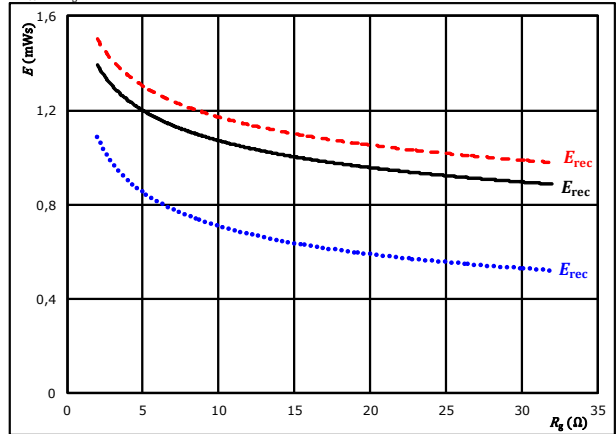
125 °C

150 °C

figure 4. FWD

Typical reverse recovered energy loss as a function of gate resistor

$$E_{rec} = f(R_g)$$



With an inductive load at

$V_{CE} = 600$ V

$V_{GE} = \pm 15$ V

$I_C = 25$ A

T_j :

25 °C

125 °C

150 °C



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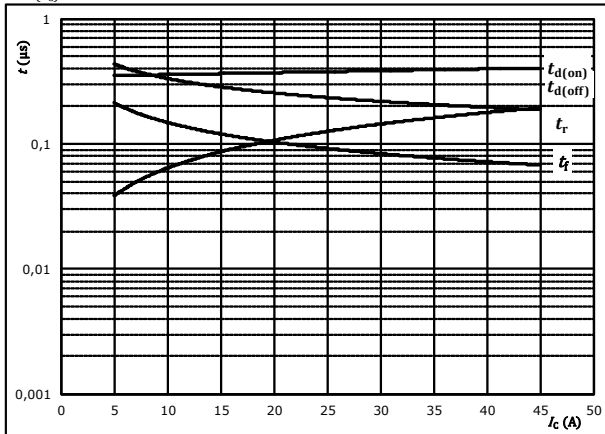
10-EZ12PMA025M7-L929A78T
10-E112PMA025M7-L929A78Z
datasheet

Brake Switching Characteristics

figure 5. IGBT

Typical switching times as a function of collector current

$$t = f(I_C)$$



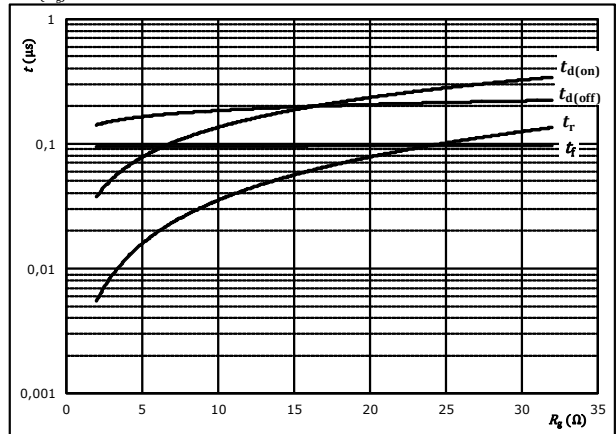
With an inductive load at

$T_j =$	150	°C
$V_{CE} =$	600	V
$V_{GE} =$	±15	V
$R_{gon} =$	32	Ω
$R_{goff} =$	32	Ω

figure 6. IGBT

Typical switching times as a function of gate resistor

$$t = f(R_g)$$



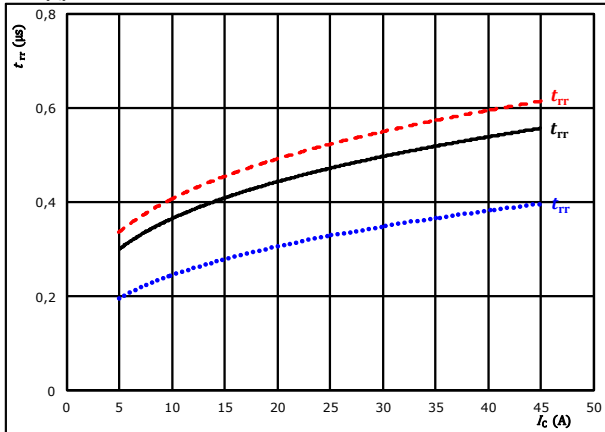
With an inductive load at

$T_j =$	150	°C
$V_{CE} =$	600	V
$V_{GE} =$	±15	V
$I_C =$	25	A

figure 7. FWD

Typical reverse recovery time as a function of collector current

$$t_{rr} = f(I_C)$$

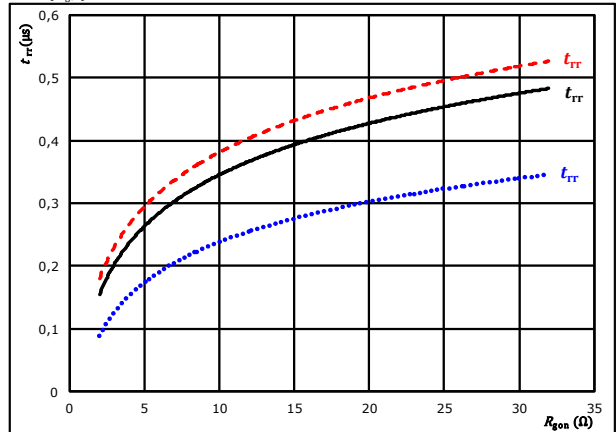


At	$V_{CE} =$	600	V	$T_j:$	25 °C	
	$V_{GE} =$	±15	V		125 °C	————
	$R_{gon} =$	32	Ω		150 °C	-----

figure 8. FWD

Typical reverse recovery time as a function of IGBT turn on gate resistor

$$t_{rr} = f(R_{gon})$$



At	$V_{CE} =$	600	V	$T_j:$	25 °C	
	$V_{GE} =$	±15	V		125 °C	————
	$I_C =$	25	A		150 °C	-----



Vincotech

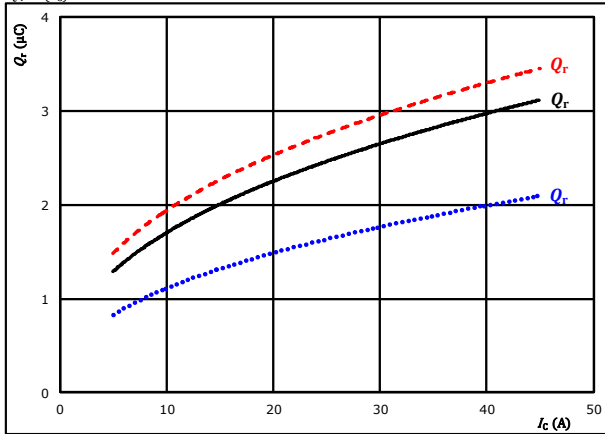
10-EZ12PMA025M7-L929A78T
10-E112PMA025M7-L929A78Z
datasheet

Brake Switching Characteristics

figure 9. FWD

Typical recovered charge as a function of collector current

$$Q_r = f(I_C)$$

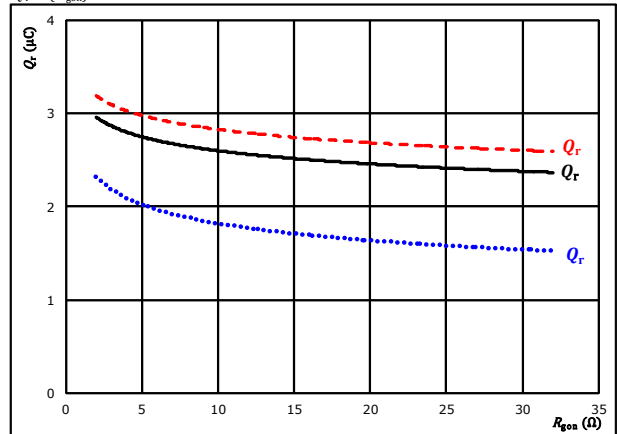


At $V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $R_{gon} = 32$ Ω
 $T_j = 25$ °C (blue dotted)
 125 °C (black solid)
 150 °C (red dashed)

figure 10. FWD

Typical recovered charge as a function of IGBT turn on gate resistor

$$Q_r = f(R_{gon})$$

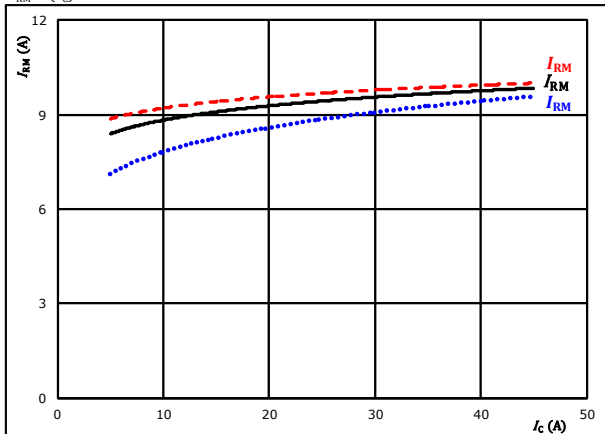


At $V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $I_C = 25$ A
 $T_j = 25$ °C (blue dotted)
 125 °C (black solid)
 150 °C (red dashed)

figure 11. FWD

Typical peak reverse recovery current as a function of collector current

$$I_{RM} = f(I_C)$$

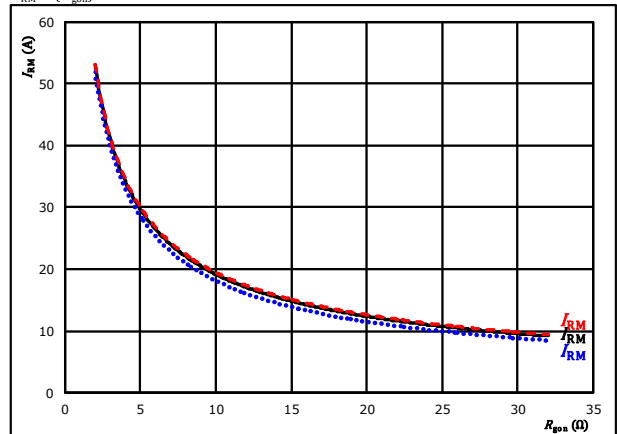


At $V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $R_{gon} = 32$ Ω
 $T_j = 25$ °C (blue dotted)
 125 °C (black solid)
 150 °C (red dashed)

figure 12. FWD

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

$$I_{RM} = f(R_{gon})$$



At $V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $I_C = 25$ A
 $T_j = 25$ °C (blue dotted)
 125 °C (black solid)
 150 °C (red dashed)



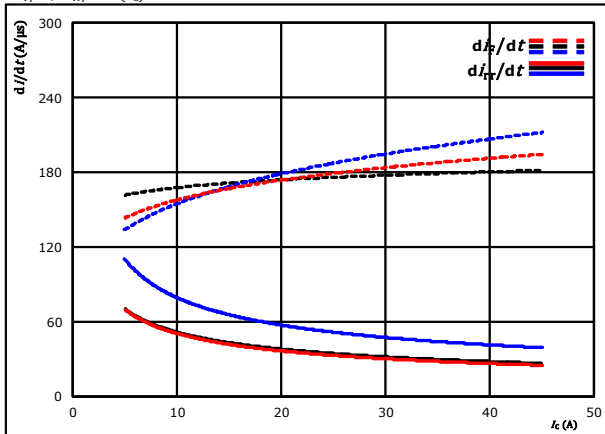
Vincotech

10-EZ12PMA025M7-L929A78T
10-E112PMA025M7-L929A78Z
 datasheet

Brake Switching Characteristics

figure 13. FWD

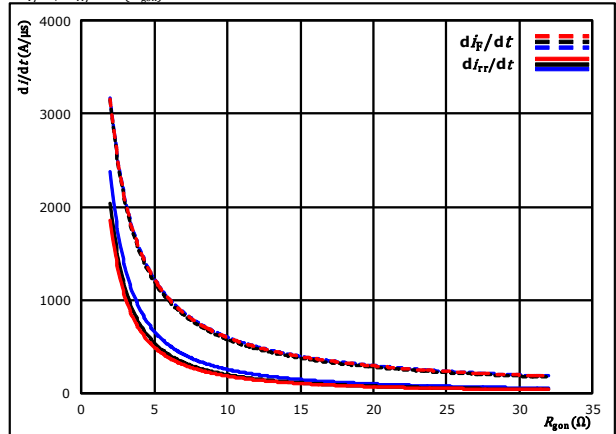
Typical rate of fall of forward and reverse recovery current as a function of collector current
 $di_F/dt, di_{rr}/dt = f(I_C)$



At $V_{CE} = 600$ V $T_J = 25$ °C
 $V_{GE} = \pm 15$ V $T_J = 125$ °C ———
 $R_{gon} = 32$ Ω $T_J = 150$ °C - - - - -

figure 14. FWD

Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor
 $di_F/dt, di_{rr}/dt = f(R_{gon})$

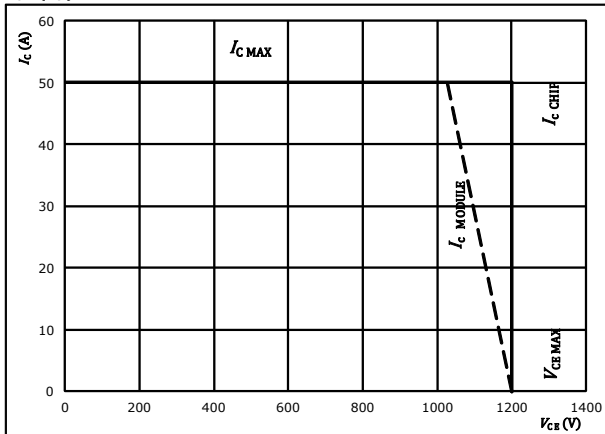


At $V_{CE} = 600$ V $T_J = 25$ °C
 $V_{GE} = \pm 15$ V $T_J = 125$ °C ———
 $I_C = 25$ A $T_J = 150$ °C - - - - -

figure 15. IGBT

Reverse bias safe operating area

$I_C = f(V_{CE})$



At $T_J = 125$ °C
 $R_{gon} = 32$ Ω
 $R_{goff} = 32$ Ω



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10-EZ12PMA025M7-L929A78T
10-E112PMA025M7-L929A78Z
 datasheet

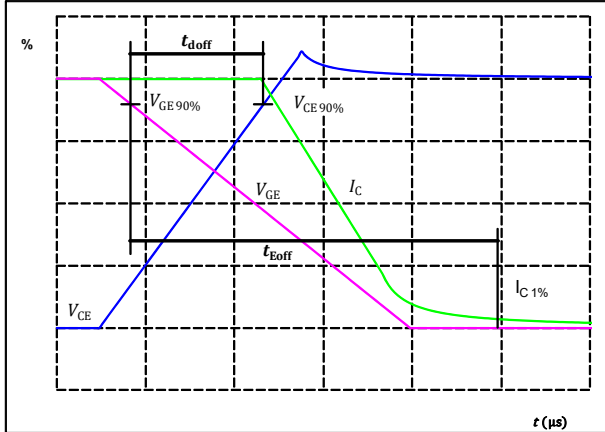
Brake Switching Definitions

General conditions

T_j	=	125 °C
R_{gon}	=	32 Ω
R_{goff}	=	32 Ω

figure 1. IGBT

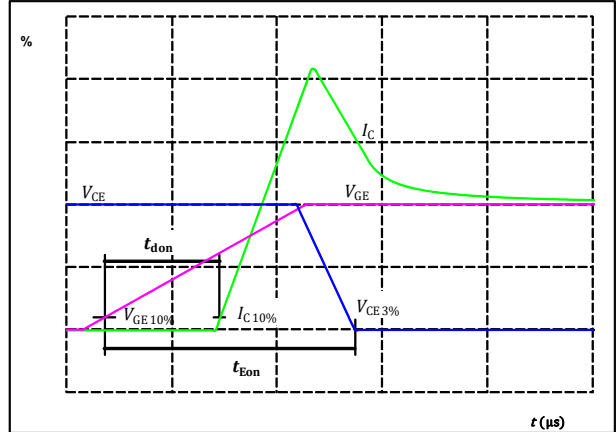
Turn-off Switching Waveforms & definition of t_{doff} , t_{Eoff} (t_{Eoff} = integrating time for E_{off})



$V_{GE}(0\%) =$	-15	V
$V_{GE}(100\%) =$	15	V
$V_C(100\%) =$	600	V
$I_C(100\%) =$	25	A
$t_{doff} =$	233	ns

figure 2. IGBT

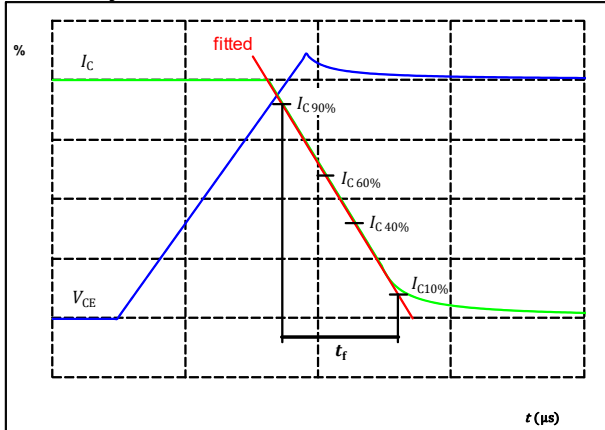
Turn-on Switching Waveforms & definition of t_{don} , t_{Eon} (t_{Eon} = integrating time for E_{on})



$V_{GE}(0\%) =$	-15	V
$V_{GE}(100\%) =$	15	V
$V_C(100\%) =$	600	V
$I_C(100\%) =$	25	A
$t_{don} =$	389	ns

figure 3. IGBT

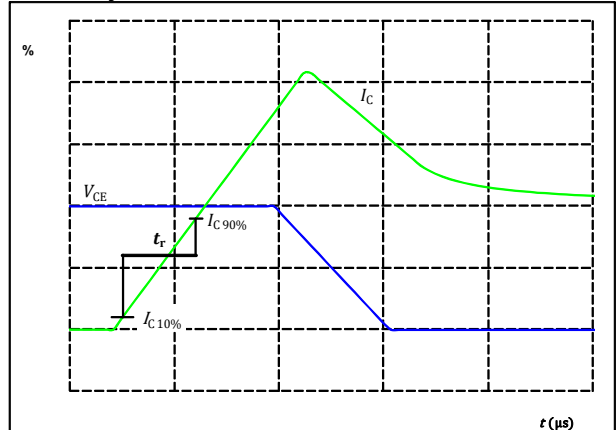
Turn-off Switching Waveforms & definition of t_f



$V_C(100\%) =$	600	V
$I_C(100\%) =$	25	A
$t_f =$	93	ns

figure 4. IGBT

Turn-on Switching Waveforms & definition of t_r



$V_C(100\%) =$	600	V
$I_C(100\%) =$	25	A
$t_r =$	117	ns

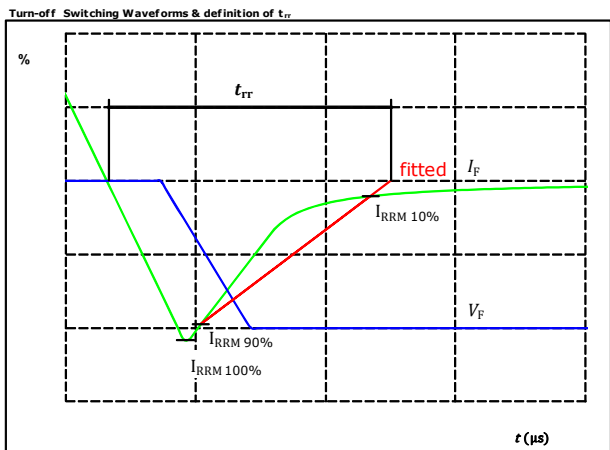


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10-EZ12PMA025M7-L929A78T
10-E112PMA025M7-L929A78Z
 datasheet

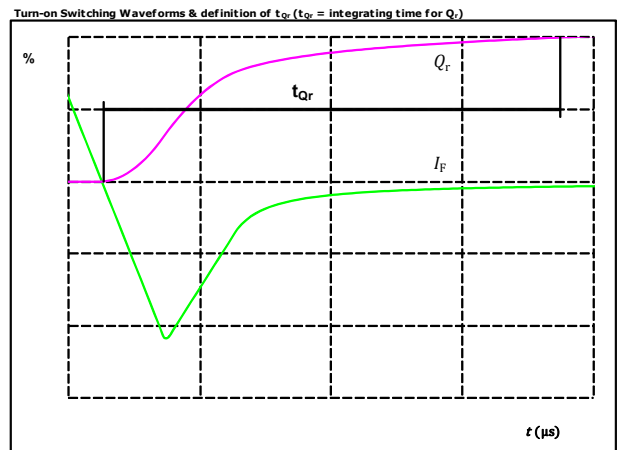
Brake Switching Characteristics

figure 5. FWD



$V_F (100\%) =$	600	V
$I_F (100\%) =$	25	A
$I_{RRM} (100\%) =$	10	A
$t_{rr} =$	448	ns

figure 6. FWD



$I_F (100\%) =$	25	A
$Q_r (100\%) =$	2,34	μC

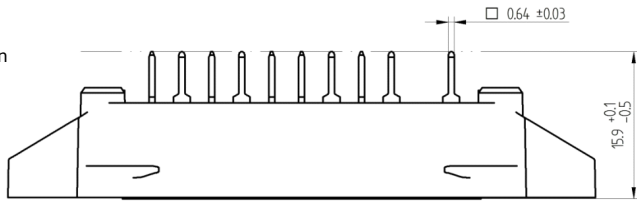
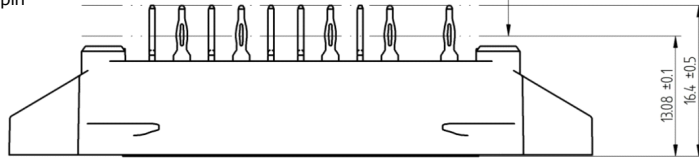
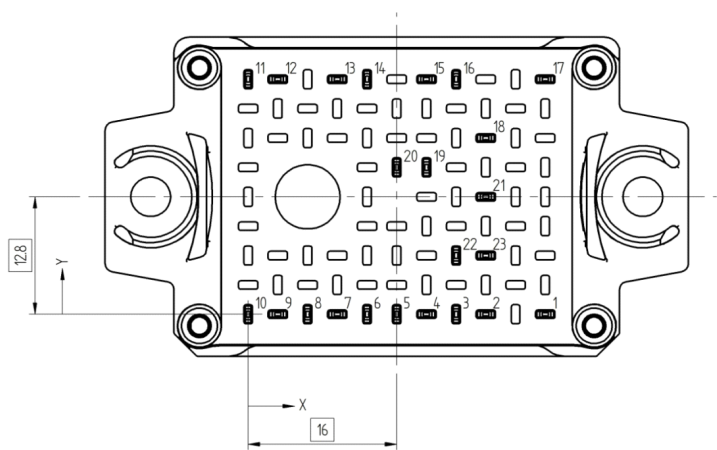


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10-EZ12PMA025M7-L929A78T 10-E112PMA025M7-L929A78Z

datasheet

Ordering Code & Marking							
Version				Ordering Code			
without thermal paste 12 mm housing with Press-fit pins				10-EZ12PMA025M7-L929A78T			
with thermal paste 12 mm housing with Press-fit pins				10-EZ12PMA025M7-L929A78T-/3/			
without thermal paste 12 mm housing with solder pins				10-E112PMA025M7-L929A78Z			
with thermal paste 12 mm housing with solder pins				10-E112PMA025M7-L929A78Z-/3/			
	Text	Name		Date code	UL & VIN	Lot	Serial
		NN-NNNNNNNNNNNNNN-TTTTWW		WWYY	UL VIN	LLLL	SSSS
	Datamatrix	Type&Ver	Lot number	Serial	Date code		
		TTTTTWW	LLLL	SSSS	WWYY		

Pin table				Outline			
Pin	X	Y	Function				
1	32	0	Br				
2	25,6	0	DC-Br				
3	22,4	0	G27				
4	19,2	0	DC-Rect				
5	16	0	G15				
6	12,8	0	DC-3				
7	9,6	0	G13				
8	6,4	0	DC-2				
9	3,2	0	G11				
10	0	0	DC-1				
11	0	25,6	Ph1				
12	3,2	25,6	G12				
13	9,6	25,6	Ph2				
14	12,8	25,6	G14				
15	19,2	25,6	Ph3				
16	22,4	25,6	G16				
17	32	25,6	ACIn1				
18	25,6	19,2	ACIn2				
19	19,2	16	Therm1				
20	16	16	Therm2				
21	25,6	12,8	ACIn3				
22	22,4	6,4	DC+Inv				
23	25,6	6,4	DC+Rect				

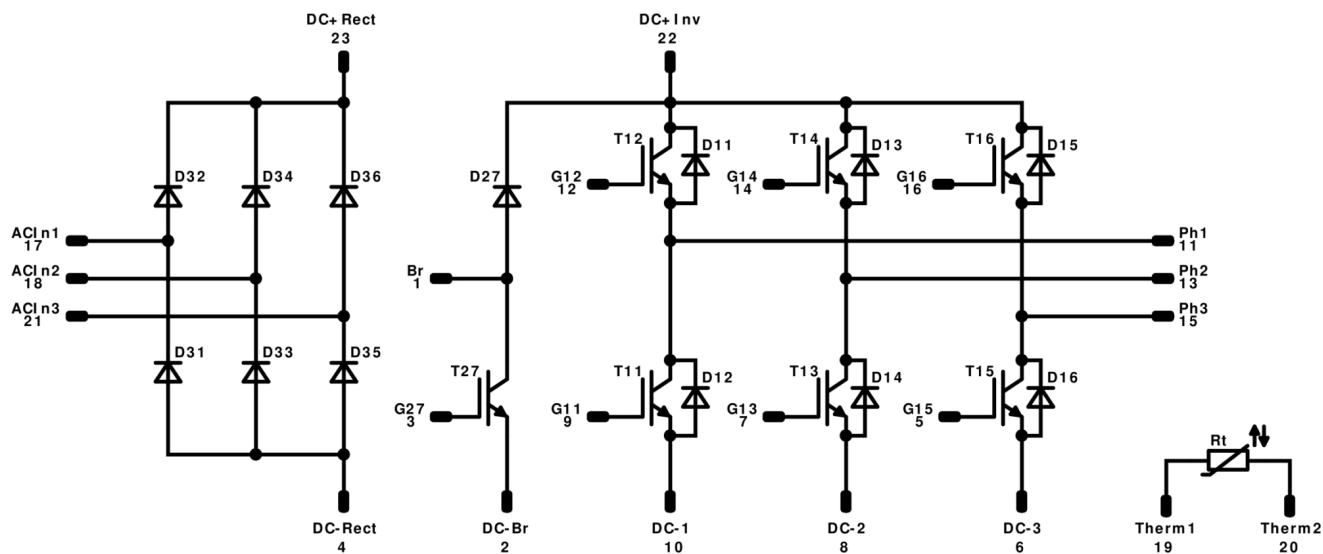
Tolerance of pinpositions: ±0.4mm at the end of pins
Dimension of coordinate axis is only offset without tolerance



10-EZ12PMA025M7-L929A78T 10-E112PMA025M7-L929A78Z datasheet

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Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T11, T12, T13, T14, T15, T16	IGBT	1200 V	25 A	Inverter Switch	
D11, D12, D13, D14, D15, D16	FWD	1200 V	25 A	Inverter Diode	
T27	IGBT	1200 V	25 A	Brake Switch	
D27	FWD	1200 V	10 A	Brake Diode	
D31, D32, D33, D34, D35, D36	Rectifier	1600 V	35 A	Rectifier Diode	
Rt	NTC			Thermistor	



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10-EZ12PMA025M7-L929A78T
10-E112PMA025M7-L929A78Z
datasheet

Packaging instruction			
Standard packaging quantity (SPQ) 100	>SPQ	Standard	<SPQ Sample

Handling instruction
Handling instructions for <i>flow</i> E1 packages see vincotech.com website.

Package data
Package data for <i>flow</i> E1 packages see vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website. 

Document No.:	Date:	Modification:	Pages
10-Ex12PMA025M7-L929A78x-D2-14	30 May. 2019	Correction of I_C/I_f values Outline updated	1,2 28

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